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	Application No.	Applicant(s)		
Nation of Allowability	10/647,060	MEARS ET AL.		
Notice of Allowability	Examiner	Art Unit		
·	Thinh T. Nguyen	2818		
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this apply or other appropriate communication IGHTS. This application is subject to	plication. If not included will be mailed in due course. THIS		
1. This communication is responsive to <u>2/7/2005</u> .				
2. X The allowed claim(s) is/are <u>1-71</u> .				
3. \boxtimes The drawings filed on <u>22 August 2003</u> are accepted by the	e Examiner.			
 4. Acknowledgment is made of a claim for foreign priority unally All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 	e been received. e been received in Application No			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the requirements		
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which giv				
 6. ☐ CORRECTED DRAWINGS (as "replacement sheets") must (a) ☐ including changes required by the Notice of Draftspers 1) ☐ hereto or 2) ☐ to Paper No./Mail Date (b) ☐ including changes required by the attached Examiner Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in 17 7. ☐ DEPOSIT OF and/or INFORMATION about the deposition of the property of	son's Patent Drawing Review (PTO 's Amendment / Comment or in the C 1.84(c)) should be written on the drawing the header according to 37 CFR 1.121(c) sit of BIOLOGICAL MATERIAL r	Office action of ngs in the front (not the back) of d). nust be submitted. Note the		
-attached Examiner's comment regarding REQUIREMENT	FOR THE DEPOSIT OF BIOLOGIC.	AL MATERIAL.		
Attachment(s)	E Matias of Information	latent Application (BTO 450)		
 Notice of References Cited (PTO-892) Dotice of Draftperson's Patent Drawing Review (PTO-948) 	5. ☐ Notice of Informal P 6. ☐ Interview Summary	atent Application (PTO-152) (PTO-413)		
	Paper No./Mail Dat	Paper No./Mail Date		
3. Information Disclosure Statements (PTO-1449 or PTO/SB/0	<u>_</u>			
Examiner's Comment Regarding Requirement for Deposit Piological Material	<u> </u>	ent of Reasons for Allowance		
of Biological Material	9. Other			
	David Nelms			
Sup	ervisory Patent Examiner			
Technology Center 2800				

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DETAILED ACTION

Reason for allowance

1. Claims 1-71 are allowed. The following is an examiner's statement of reason for allowance:

I/ Group I: Claims 1-20:

None of the references of record teaches or suggests the claimed

SEMICONDUCTOR DEVICE INCLUDING BAND-ENGINEERED SUPERLATTICE
having the limitations:

--" each group of layers of said superlattice comprising a plurality of stacked base semiconductor monolayers defining a base semiconductor portion and an energy band-modifying layer thereon;

said energy-band modifying layer comprising at least one nonsemiconductor monolayer constrained within a crystal lattice of adjacent base
semiconductor portions so that said superlattice has a higher charge carrier
mobility in the parallel direction than would otherwise be present. "--

and all other limitations as recited in claim 1.

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II/ Group II: Claims 21-34:

None of the references of record teaches or suggests the claimed

SEMICONDUCTOR DEVICE INCLUDING BAND-ENGINEERED SUPERLATTICE
having the limitations:

--" each group of layers of said superlattice comprising a plurality of stacked silicon monolayers defining a silicon portion and an energy band-modifying layer thereon; said energy-band modifying layer comprising at least one oxygen monolayer constrained within a crystal lattice of adjacent silicon portions so that said superlattice has a higher charge carrier mobility in the parallel direction than would otherwise be present. "--

and all other limitations as recited in claim 21.

III/ Group III: Claims 35-45:

None of the references of record teaches or suggests the claimed

SEMICONDUCTOR DEVICE INCLUDING BAND-ENGINEERED SUPERLATTICE
having the limitations:

--" each group of layers of said superlattice comprising less than eight stacked base semiconductor monolayers defining a base semiconductor portion and an energy band-modifying layer thereon; said energy-band modifying layer comprising a single non-semiconductor monolayer constrained within a crystal

lattice of adjacent base semiconductor portions so that said superlattice has a higher charge carrier mobility in the parallel direction than would otherwise be present. "--

and all other limitations as recited in claim 35.

IV/ Group IV: Claims 46-52:

None of the references of record teaches or suggests the claimed

SEMICONDUCTOR DEVICE INCLUDING BAND-ENGINEERED SUPERLATTICE
having the limitations:

--" regions for causing transport of charge carriers through said superlattice in a parallel direction relative to the stacked groups of layers; each group of layers of said superlattice comprising less than eight stacked silicon monolayers defining a silicon portion and an energy band-modifying layer thereon; said energy-band modifying layer comprising a single oxygen monolayer constrained within crystal lattice of adjacent silicon portions. "--

and all other limitations as recited in claim 46.

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V/ Group V: Claims 53-71:

None of the references of record teaches or suggests the claimed

SEMICONDUCTOR DEVICE INCLUDING BAND-ENGINEERED SUPERLATTICE
having the limitations:

--" each group of layers of said superlattice comprising a plurality of stacked base semiconductor monolayers defining a base semiconductor portion and an energy band-modifying layer thereon; said energy-band modifying layer comprising at least one non-semiconductor monolayer constrained within a crystal lattice of adjacent base semiconductor portions so that said superlattice has a lower conductivity effective mass in the parallel direction than would otherwise be present. "--

and all other limitations as recited in claim 53.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance".

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Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thinh T Nguyen whose telephone number is 571-272-1790. The examiner can normally be reached on Monday-Friday 9:00am-6:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached at 571-272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Thinh T Nguyen

TPW

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David Nelms
Supervisory Patent Examiner
Technology Center 2800